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N-channel 80 V, 35 mΩ logic level MOSFET in LFPAK33

19 September 2016

Product data sheet

1. General description

Logic level N-channel MOSFET in an LFPAK33 (Power33) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Features and benefits

- Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with V_{GS(th)} rating of greater than 0.5 V at 175 °C

3. Applications

- 12 V, 24 V and 48 V automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

4. Quick reference data

Table 1. Qui	ck reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	-	80	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>	-	-	26	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>	-	-	62	W
Static charact	eristics	·				
R _{DSon}	drain-source on-state resistance	V _{GS} = 5 V; I _D = 5 A; T _j = 25 °C; <u>Fig. 11</u>	-	28	35	mΩ
Dynamic char	acteristics					
Q _{GD}	gate-drain charge	I_D = 10 A; V_{DS} = 64 V; V_{GS} = 5 V; T_j = 25 °C; Fig. 13; Fig. 14	-	4.9	-	nC

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	Source		D
2	S	Source		
3	S	Source	\bigcirc	G-UF4
4	G	Gate		mbb076 S
mb	D	Mounting base; connected to drain	LFPAK33 (SOT1210)	

6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
BUK9M35-80E	LFPAK33	Plastic single ended surface mounted package (LFPAK33); 8 leads	SOT1210			

7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK9M35-80E	93580E

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Мах	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	80	V
V _{DGR}	drain-gate voltage	R _{GS} = 20 kΩ		-	80	V
V _{GS}	gate-source voltage	DC; T _j ≤ 175 °C		-10	10	V
		Pulsed; T _j ≤ 175 °C	[1][2]	-15	15	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	62	W
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>		-	26	А
		V _{GS} = 5 V; T _{mb} = 100 °C; <u>Fig. 2</u>		-	19	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$; Fig. 3		-	106	А

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Symbol	Parameter	Conditions		Min	Max	Unit
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drai	in diode	·				
I _S	source current	T _{mb} = 25 °C		-	26	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$		-	106	А
Avalanche r	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\label{eq:ID} \begin{array}{l} {\sf I}_{\sf D} = 26 \; {\sf A}; \; {\sf V}_{sup} \le 80 \; {\sf V}; \; {\sf R}_{GS} = 50 \; \Omega; \\ {\sf V}_{GS} = 5 \; {\sf V}; \; {\sf T}_{j(init)} = 25 \; {}^{\circ}{\sf C}; \; unclamped; \\ \hline {\sf Fig. 4} \end{array}$	[3][4]	-	32.3	mJ

- [1] Accumulated pulse duration up to 50 hours delivers zero defect ppm.
- [2] Significantly longer life times are achieved by lowering T_i and or V_{GS}
- [3] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [4] Refer to application note AN10273 for further information.

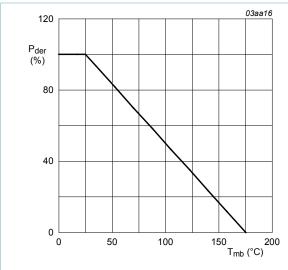
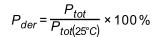


Fig. 1. Normalized total power dissipation as a function of mounting base temperature



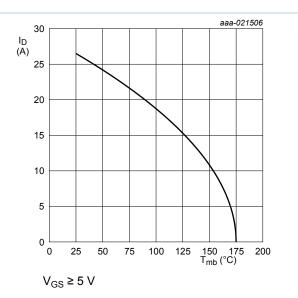
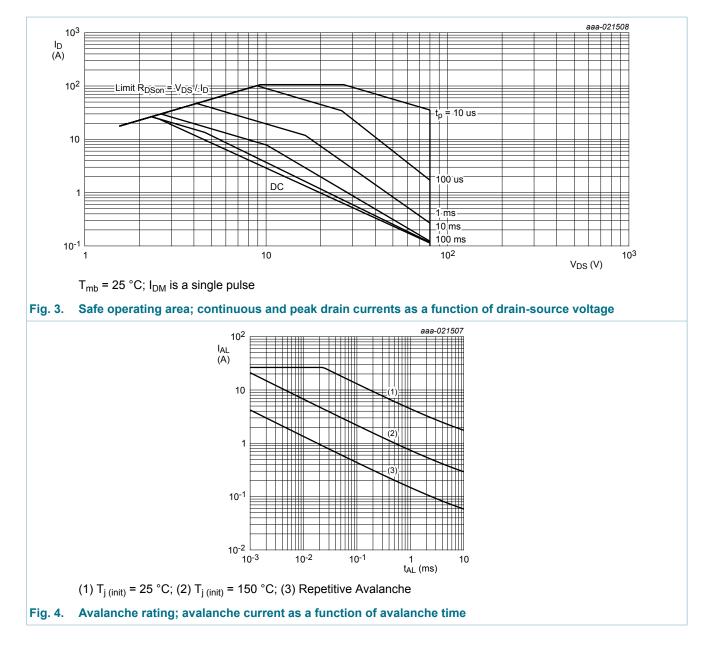


Fig. 2. Continuous drain current as a function of mounting base temperature

$$I_D = 26A \times \sqrt{\frac{175^{\circ}C - T_{mb}}{150^{\circ}C}} \text{ for } T_{mb} \ge 25^{\circ}C$$

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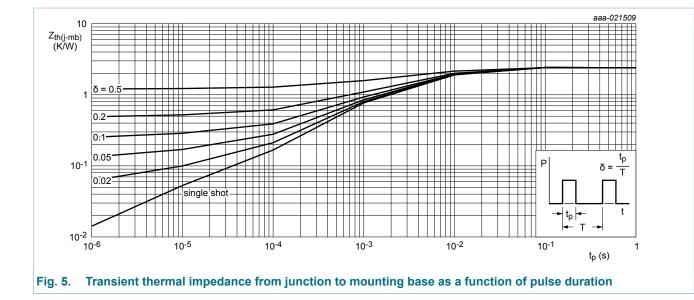


9. Thermal characteristics

Table 6. The	ermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	2.01	2.43	K/W

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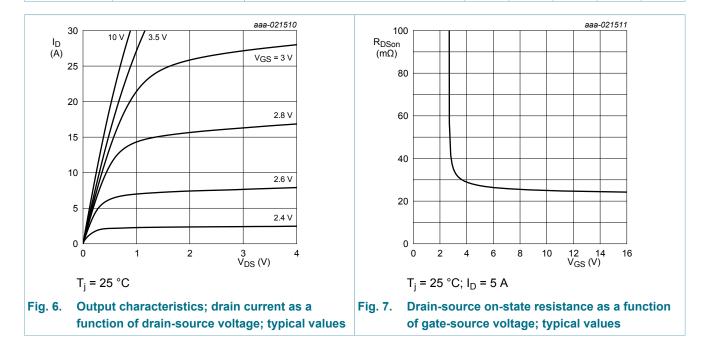
10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · · · ·				
V _{(BR)DSS}	drain-source	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	80	-	-	V
	breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	72	-	-	V
V _{GS(th)}	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; Fig. 9; Fig. 10	1.4	1.7	2.1	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 10	-	-	2.45	V
	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; Fig. 10	0.5	-	-	V	
I _{DSS} drain leakage current	drain leakage current	V_{DS} = 80 V; V_{GS} = 0 V; T_j = 25 °C	-	0.01	1	μA
		V _{DS} = 80 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μA
I _{GSS}	gate leakage current	V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
		V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state	V _{GS} = 5 V; I _D = 5 A; T _j = 25 °C; <u>Fig. 11</u>	-	28	35	mΩ
	resistance	V _{GS} = 10 V; I _D = 5 A; T _j = 25 °C; <u>Fig. 11</u>	-	25	31	mΩ
		V _{GS} = 5 V; I _D = 5 A; T _j = 175 °C; <u>Fig. 12</u>	-	-	88	mΩ
Dynamic cł	naracteristics	· ·	1			
Q _{G(tot)}	total gate charge	I _D = 10 A; V _{DS} = 64 V; V _{GS} = 5 V;	-	13.5	-	nC
Q _{GS}	gate-source charge $T_j = 25 \text{ °C}; \text{ Fig. 13}; \text{ Fig. 14}$	T _j = 25 °C; <u>Fig. 13; Fig. 14</u>	-	3.3	-	nC
Q _{GD}	gate-drain charge		-	4.9	-	nC

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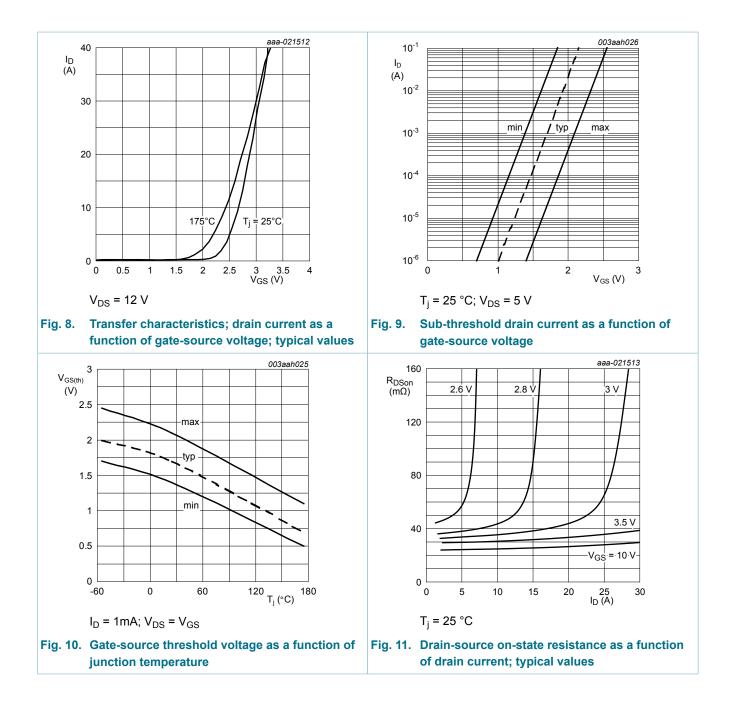
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Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
C _{iss}	input capacitance	V_{DS} = 25 V; V_{GS} = 0 V; f = 1 MHz;		-	1356	1804	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>		-	106	127	pF
C _{rss}	reverse transfer capacitance			-	52	71	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 60 \text{ V}; \text{ R}_{L} = 5 \Omega; \text{ V}_{GS} = 5 \text{ V};$ $R_{G(ext)} = 5 \Omega; \text{ T}_{j} = 25 ^{\circ}\text{C}$		-	8.8	-	ns
t _r	rise time			-	14	-	ns
t _{d(off)}	turn-off delay time			-	19.5	-	ns
t _f	fall time			-	12	-	ns
Source-dra	in diode	1	1	1			
V _{SD}	source-drain voltage	$I_{S} = 5 \text{ A}; V_{GS} = 0 \text{ V}; T_{j} = 25 \text{ °C}; Fig. 16$		-	0.78	1.2	V
t _{rr}	reverse recovery time	I_{S} = 10 A; dI _S /dt = -100 A/µs; V _{GS} = 0 V;		-	21	-	ns
Q _r	recovered charge	V _{DS} = 25 V; T _j = 25 °C		-	21.6	-	nC



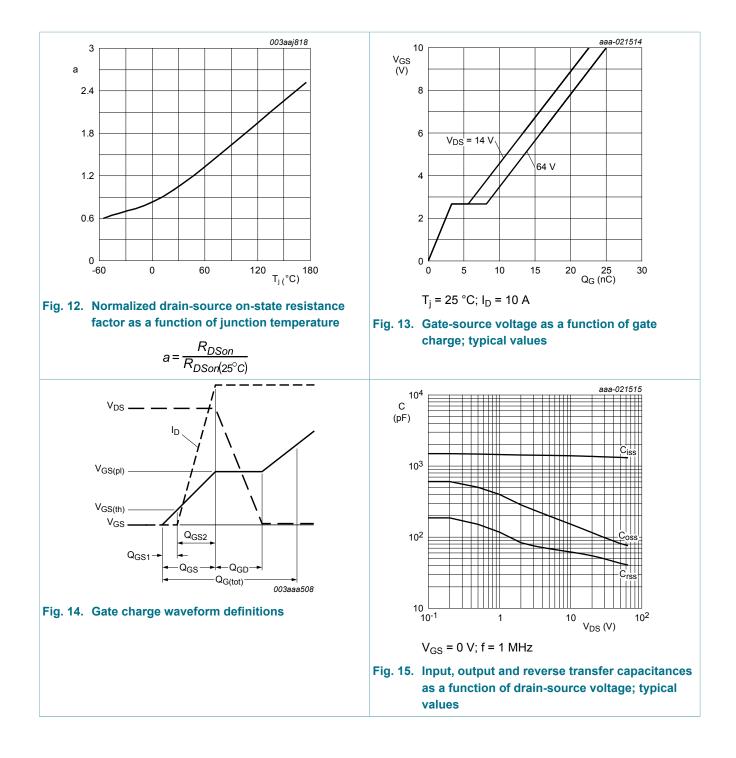
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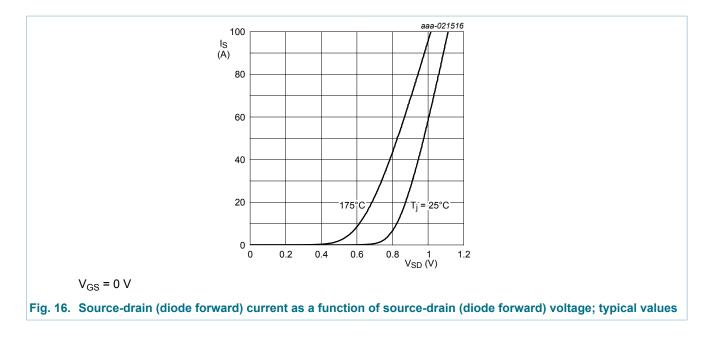
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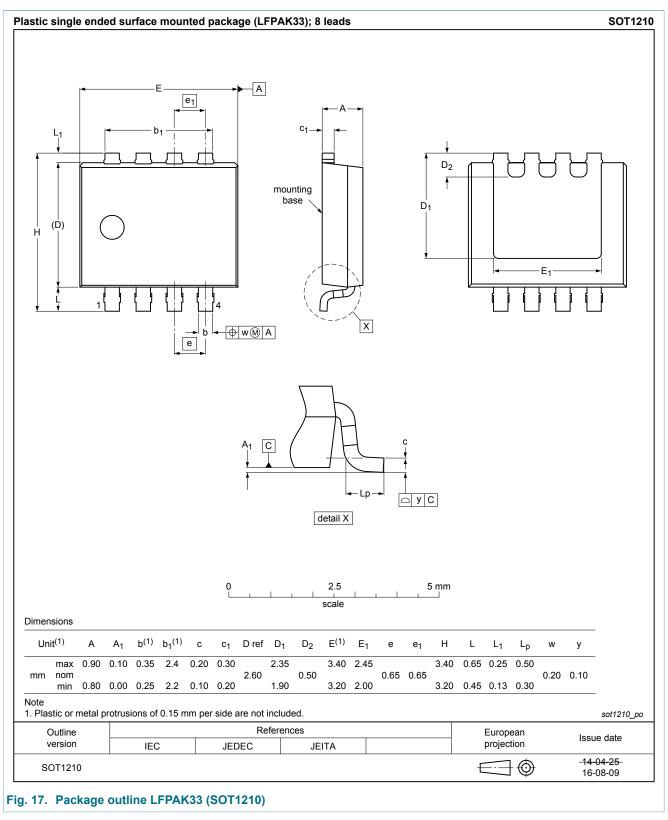


11. Application information

For guidance on how to use and understand this datasheet, please refer to application note <u>AN11158</u> "Understanding power MOSFET datasheet parameters".

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12. Package outline



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N-channel 80 V, 35 mΩ logic level MOSFET in LFPAK33

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